IN THE CLAIMS

Please amend the claims as follows.

1.-18. (Canceled)

19. (Previously Presented) A capacitor comprising:

a first conductive capacitor plate of a first material;

a second conductive capacitor plate; and

a dielectric structure interposed between said first and second conductive capacitor plates, wherein said dielectric structure includes a non-oxidized portion and an oxidized portion, wherein the oxidized portion includes a second material, wherein the oxidized portion directly contacts the second conductive capacitor plate, and wherein the oxidized portion comprises titanium oxide.

20. (Previously Presented) A memory system comprising:

a monolithic memory device, comprising a capacitor, wherein the capacitor comprises:

a first conductive capacitor plate of a first material;

a second conductive capacitor plate; and

a dielectric structure interposed between said first and second conductive capacitor plates, wherein said dielectric structure includes a non-oxidized portion and an oxidized portion, wherein the oxidized portion includes a second material, wherein the oxidized portion directly contacts the second conductive capacitor plate, and wherein the oxidized portion comprises titanium oxide; and

a processor configured to access the monolithic memory device.

21.-79. (Canceled)

80. (Withdrawn, Previously Presented) The capacitor of claim 19, wherein the oxidized portion further includes at least one additional metal alloyed with the titanium, and wherein the additional metal is selected from the group consisting of strontium, barium, and lead.

81. (Previously Presented) The capacitor of claim 19, wherein the second conductive capacitor plate is formed from a material selected from the group consisting of polysilicon and metal.

82. (Canceled)

83. (Withdrawn, Previously Presented) The memory system of claim 20, wherein the oxidized portion further includes at least one additional metal alloyed with the titanium, and wherein the additional metal is selected from the group consisting of strontium, barium, and lead.

84. (Previously Presented) The memory system of claim 20, wherein the second conductive capacitor plate is formed from a material selected from the group consisting of polysilicon and metal.

85.-106. (Canceled)

107. (Previously Presented) A capacitor comprising:

a first conductive capacitor plate of a first material;

a second conductive capacitor plate; and

a dielectric structure interposed between said first and second conductive capacitor plates, wherein said dielectric structure includes a non-oxidized portion and an oxidized portion, wherein the oxidized portion includes a second material, wherein the oxidized portion directly contacts the second conductive capacitor plate, and wherein the oxidized portion of the dielectric structure comprises titanium.

108. (Previously Presented) The capacitor of claim 19, further comprising at least one of a diffusion barrier layer and an oxidation resistant layer interposed between the first conductive capacitor plate and the oxidized portion of the dielectric structure.

109. (Previously Presented) A memory system comprising:

a monolithic memory device, comprising a capacitor, wherein the capacitor comprises:

a first conductive capacitor plate of a first material;

a second conductive capacitor plate; and

a dielectric structure interposed between said first and second conductive capacitor plates, wherein said dielectric structure includes a non-oxidized portion and an oxidized portion, wherein the oxidized portion includes a second material, wherein the oxidized portion directly contacts the second conductive capacitor plate, and wherein the oxidized portion of the dielectric structure comprises titanium; and

a processor configured to access the monolithic memory device.

110. (Previously Presented) The memory system of claim 20, further comprising at least one of a diffusion barrier layer and an oxidation resistant layer interposed between the first conductive capacitor plate and the oxidized portion of the dielectric structure.

111.-124. (Canceled)